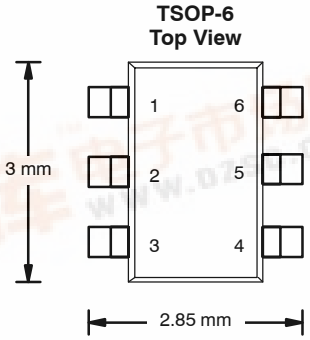
查询SI3460DV供应商 捷多邦，专业PCB打样工厂，24小时加急出货

N-Channel 20-V (D-S) MOSFET

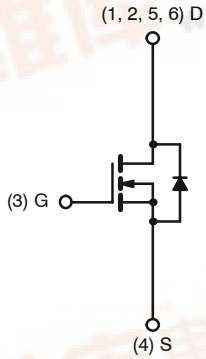
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.027 @ V_{GS} = 4.5 V	6.8
	0.032 @ V_{GS} = 2.5 V	6.3
	0.038 @ V_{GS} = 1.8 V	5.7

FEATURES

- TrenchFET® Power MOSFET
- 100% R_g Tested



Ordering Information: Si3460DV-T1



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	±8		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	6.8	5.1	A
	T_A = 70°C		5.4	4.1	
Pulsed Drain Current		I_{DM}	20		
Continuous Source Current (Diode Conduction)[a]		I_S	1.7	0.9	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.0	1.1	W
	T_A = 70°C		1.3	0.73	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 sec	R_{thJA}	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

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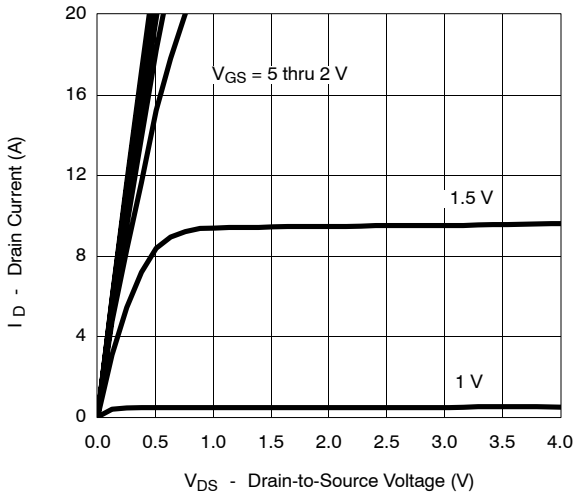
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA	0.45			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 16 V, V_{GS} = 0 V			1	µA
		V_{DS} = 16 V, V_{GS} = 0 V, T_J = 70°C			5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 5.1 A		0.023	0.027	Ω
		V_{GS} = 2.5 V, I_D = 4.7 A		0.027	0.032	
		V_{GS} = 1.8 V, I_D = 2 A		0.032	0.038	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 5.1 A		25		S
Diode Forward Voltage[a]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 5.1 A		13.5	20	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			2.2		
Gate Resistance	R_g		0.5		2.9	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 10 Ω I_D ≅ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		15	30	ns
Rise Time	t_r			30	60	
Turn-Off Delay Time	$t_{d(off)}$			70	140	
Fall Time	t_f			30	60	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, di/dt = 100 A/µs		40	80	

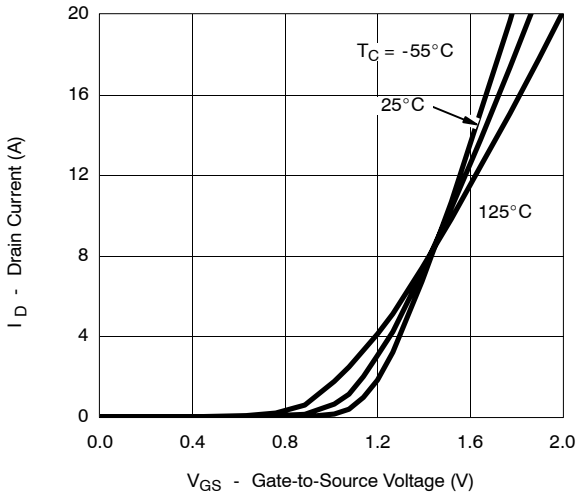
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

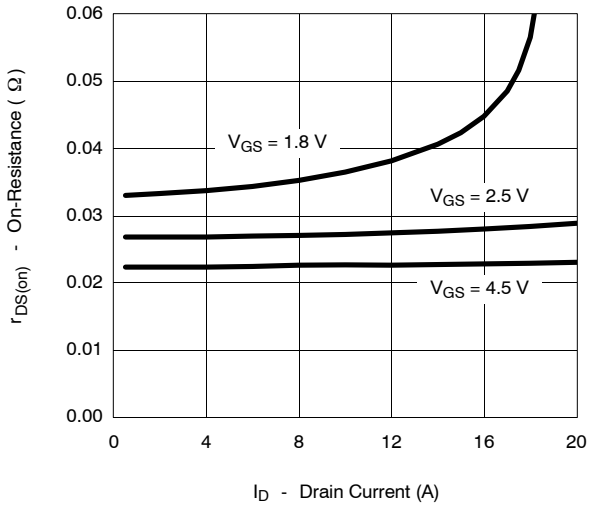


Transfer Characteristics

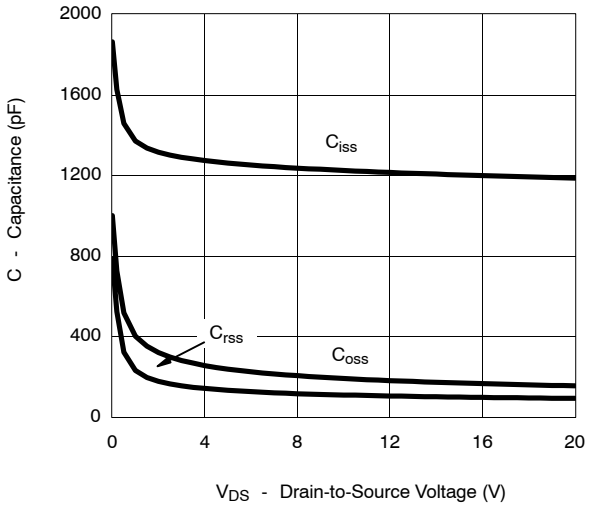


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

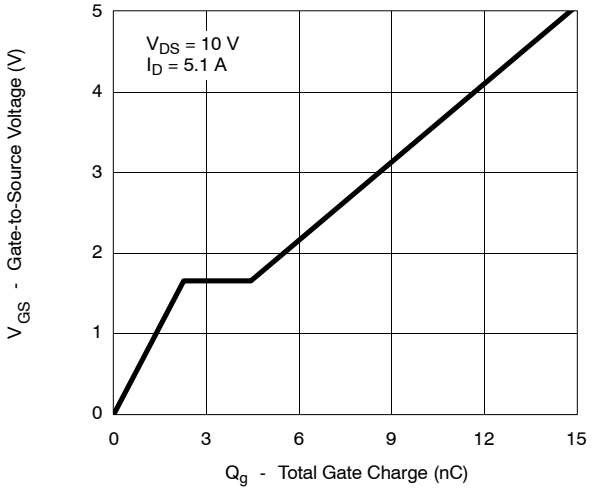
On-Resistance vs. Drain Current



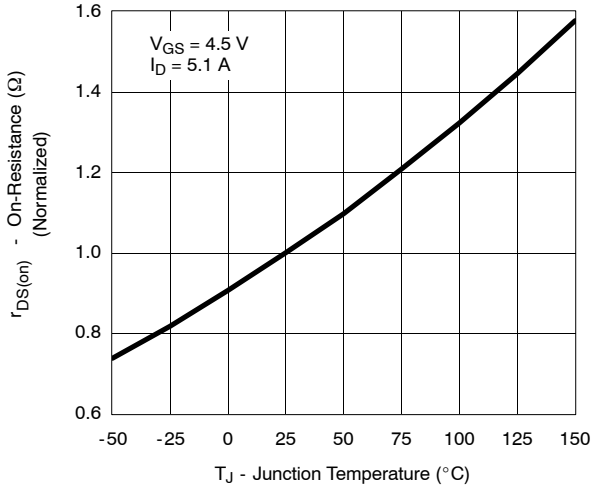
Capacitance



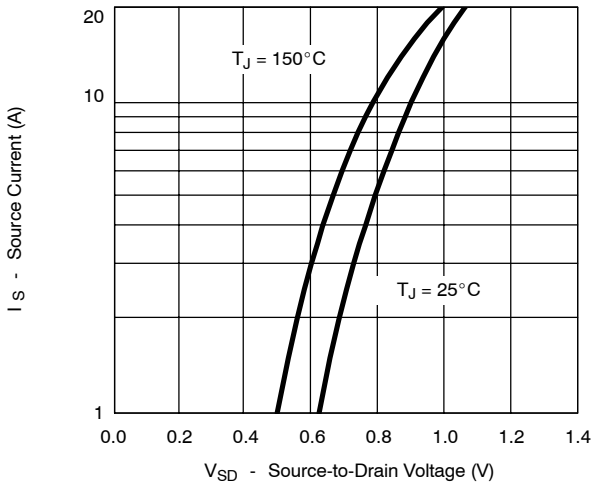
Gate Charge



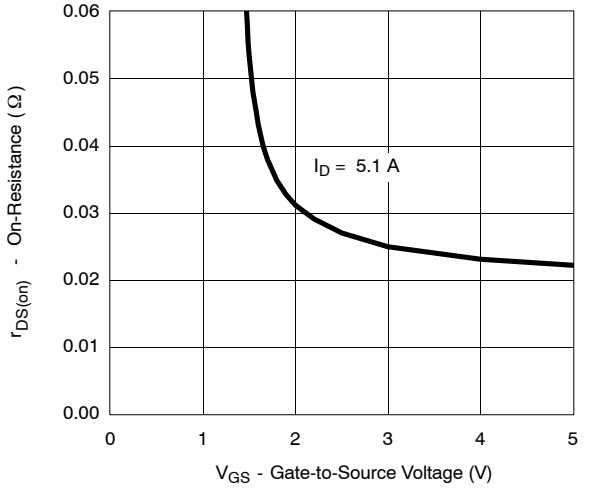
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

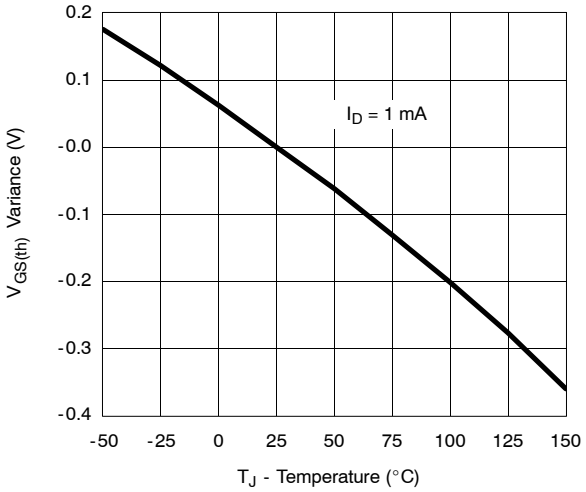


On-Resistance vs. Gate-to-Source Voltage

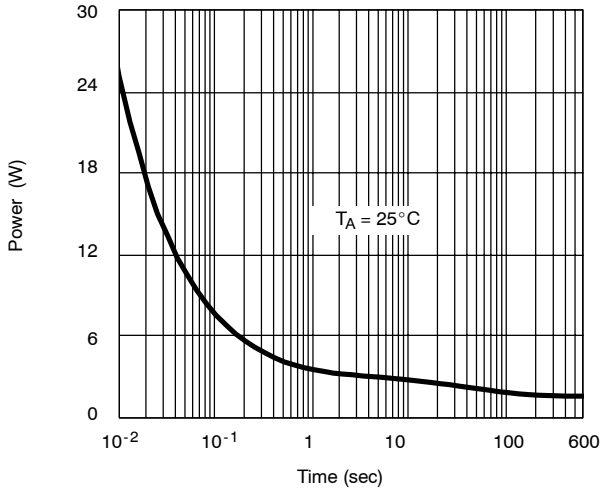


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

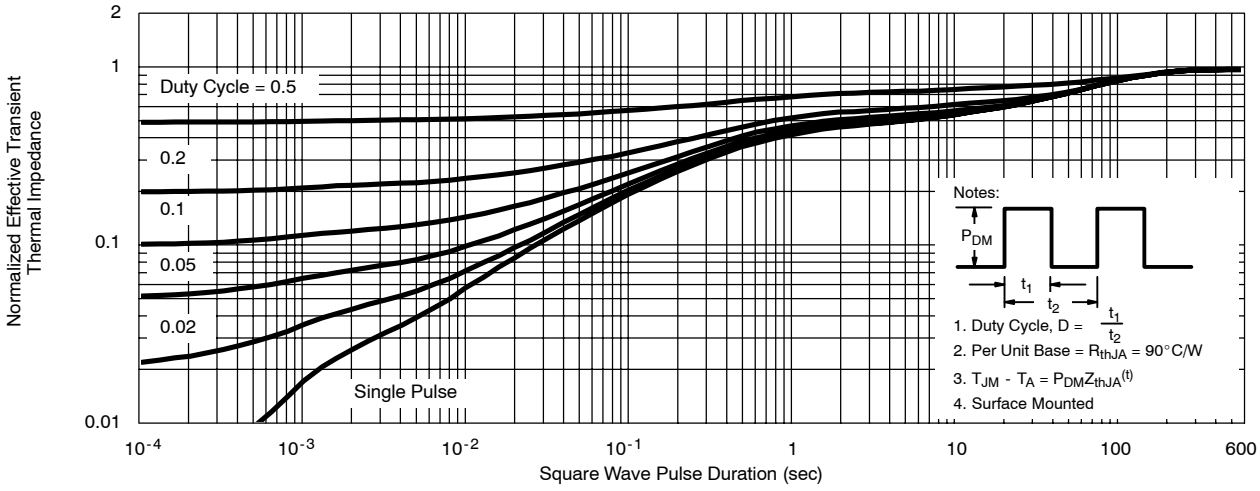
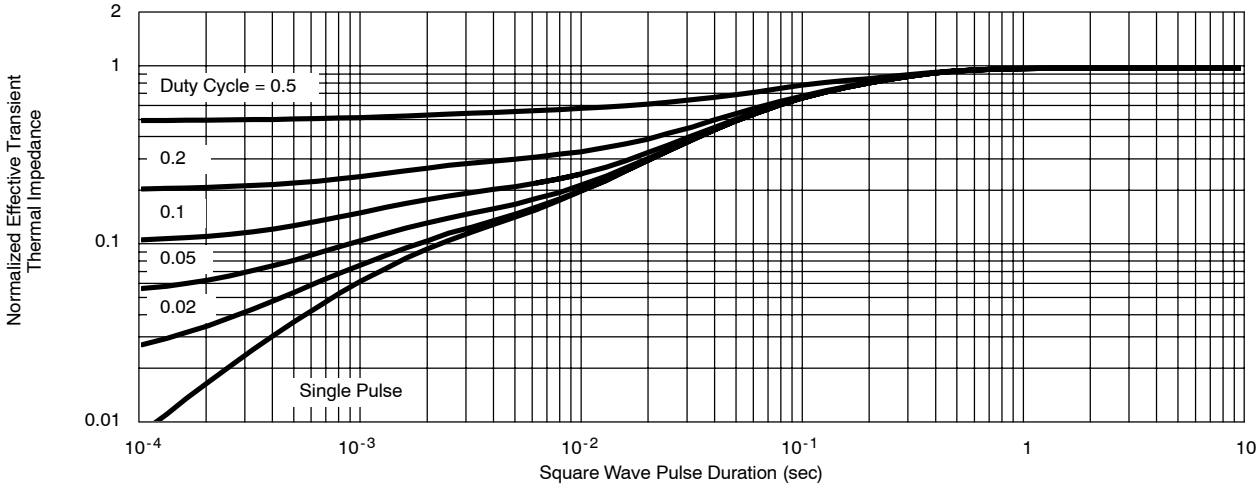
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot